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Dave Barber (center) received the award from General Chairman George Ebel (left), and Board Member Al Tamburrino (right).

The International Reliability Physics Symposium Award for Outstanding Contributions in the Field of Reliability Physics was first authorized in 1971 by the Symposium Board of Directors. This award, which is not necessarily given annually, is presented to individuals who have made major significant contributions to the advancement of the field of reliability.

The 1984 award is presented to DAVID F. BARBER in recognition of his numerous contributions to the field of Reliability Physics. Mr. Barber, Chief of the Reliability Branch at RADC for over seventeen years before his retirement in 1979, was an innovator in applying materials science, device design and process engineering, and electronics to what had been a primarily statistical discipline. He brought “physics of failure” out of the laboratory closet for direct support to the systems projects and fielded equipment. He was the energetic and effective executive who provided scientific personnel from the reliability physics laboratories to support the Component Quality Assurance Program for the Minuteman II, one of the first applications of integrated circuits in military hardware. Mr. Barber was also one of the first in government to recognize the revolutionary impact of microprocessor devices for military electronics, and, in 1977, organized a team of engineers and reliability scientists to encourage the application, standardization, and reliability qualification of these devices. Mr. Barber has also given years of dedicated service to this symposium as a member of the Management Committee, as a member of the Board of Directors, and as General Chairman of the Symposium. A Senior Member of the IEEE, he served on the ADCOM of the Reliability Society. He has also been closely associated with the Annual Reliability and Maintainability Symposium, the Government Microelectronic Applications Conference (GOMAC) and the EOS/ESD Symposium. Mr. Barber has been a man of breadth as well as depth, being well known for his work in the Association of School Boards at the State level in New York, public spirited organizations such as Rotary, and is an avid sportsman—and a sportscaster for the Women’s PGA. He is presently the President of Scien-Tech Associates, a Conference Management Consultant firm, which is engaged by IRPS for publications and arrangements.
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